Magnetoresistive RAM

Honeywell MRAM: Reliable and Rad Hard Nonvolatile Memory for Space Applications
Next Generation Memory

To provide space system electronics a robust and reliable nonvolatile memory for long term data storage, Honeywell offers the new space-qualified, radiation hardened magnetoresistive random access memory (MRAM). The Honeywell non-volatile MRAM offers longer data retention, excellent endurance and wider operating temperature range compared to other non-volatile technologies.

With 1Mb, 16Mb and 64Mb (in development) density devices, system designers can now benefit from a commercial-based memory technology that withstands the harsh environments of space. The MRAM delivers long-term data integrity for critical applications like processor code storage and fast access times for re-writeable data logs.

Why MRAM?

A combination of the MRAM and Honeywell Rad Hard Silicon on Insulator (SOI) CMOS technologies makes it revolutionary.

Unlike most other memory technologies, MRAM data is stored as a magnetic state rather than an electrical charge which results in longer data retention and reduction in power. A great new memory is created by combining the ability to retain data (with or without power) and nearly unlimited Read and Write cycles with the radiation hardened 150nm SOI CMOS technology. Our MRAM series delivers high reliability and radiation hardness over a wide operating temperature range of -40°C to +125°C.

**Honeywell Committed to Your Innovations**

<table>
<thead>
<tr>
<th>PRODUCT</th>
<th>CONFIGURATION</th>
<th>VOLTAGE(V)</th>
<th>Read Access / Write Cycle Time</th>
<th>TOTAL DOSE/SEU</th>
</tr>
</thead>
<tbody>
<tr>
<td>1 Mb</td>
<td>64K X 16</td>
<td>1.8V, 3.3V</td>
<td>Read: &lt;80ns Write: 140ns</td>
<td>300k or 1Mrad(Si)/1E-10 upsets/bit-day</td>
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<tr>
<td>HXNV0100</td>
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<tr>
<td>16 Mb</td>
<td>2M x 8 or 1M x 16</td>
<td>3.3V</td>
<td>Read: &lt;95ns Write: 140ns</td>
<td>300k or 1Mrad(Si)/1E-10 upsets/bit-day</td>
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<tr>
<td>HXNV01600</td>
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</tr>
<tr>
<td>64 Mb</td>
<td>8M x 8 or 4M x 16</td>
<td>3.3V</td>
<td>Read: &lt;100ns Write: 150ns</td>
<td>300k or 1Mrad(Si)/1E-10 upsets/bit-day</td>
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<td>HXNV06400</td>
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For over three decades, Honeywell radiation hardened components have been relied upon to perform exceptionally in radiation intensive environments. Nearly every major mission in space is successfully powered by Honeywell electronics. On August 6, 2012, “Curiosity”, the Mars Space Landing vehicle arrived safely with Honeywell’s rad hard SRAM and mixed signal ASICs aboard. Honeywell is committed to investing in your next generation technology, and continually enhances aerospace electronics to drive your systems faster, smarter, more reliably and efficiently than previous versions.

Find out more
Learn more about Honeywell Microelectronics solutions at www.honeywellmicroelectronics.com

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